

P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)
- 40	$0.012 \text{ at V}_{GS} = -10 \text{ V}$	- 60 ^d	60
	0.018 at $V_{GS} = -4.5 \text{ V}$	- 48 ^d	00

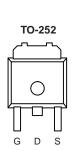
FEATURES

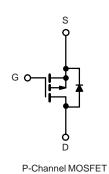
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Power Switch
- Load Switch in High Current Applications
- DC/DC Converters





ABSOLUTE MAXIMUM RATINGS	T _C = 25 °C, unless oth	erwise noted		
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 40	V	
Gate-Source Voltage		V _{GS}	± 20	7 v
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C	1-	- 60 ^d	
Continuous Diam Current (1) = 130 C)	T _C = 70 °C	I _D	- 60 ^d	A
Pulsed Drain Current		I _{DM}	- 180	7
Avalanche Current		I _{AS}	- 46	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	106	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	В	73.5 ^b	10/
	T _A = 25 °C°	P _D	2.5	W
Operating Junction and Storage Temperature Rai	T _J , T _{stq}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W
Junction-to-Case (Drain)	R _{thJC}	1.7	C/VV

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 40			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 2.5		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
Zero Gate Voltage Drain Current		V _{DS} = - 40 V, V _{GS} = 0 V			- 1	μΑ	
	I _{DSS}	V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 125 °C			- 50		
		V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 150 °C			- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 50			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V, I _D = - 22 A		0.010	0.012	Ω	
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 19 A		0.015	0.018		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 22 A		45		S	
Dynamic ^b				1	'		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 20 V, f = 1 MHz		5380		pF	
Output Capacitance	C _{oss}			570			
Reverse Transfer Capacitance	C _{rss}	1		500			
	Q _g	V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 20 A		106	159	nC	
Total Gate Charge ^c				60	90		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -20 \text{ A}$		22			
Gate-Drain Charge ^c	Q _{gd}]		27			
Gate Resistance	R _g	f = 1 MHz	0.4	1.8	3.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	$V_{DD} = -20 \text{ V}, R_L = 2 \Omega$ $I_D \cong -10 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		12	18	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			70	105		
Fall Time ^c	t _f	1		18	27		
Drain-Source Body Diode Ratings a	nd Characteri	stics T _C = 25 °C ^b					
Continuous Current	I _S				- 60		
Pulsed Current	I _{SM}				- 180	A	
Forward Voltage ^a	V _{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t _{rr}			35	53	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 10 A, dI/dt = 100 A/μs		- 2	- 3	Α	
Reverse Recovery Charge	Q _{rr}	†		33	50	nC	

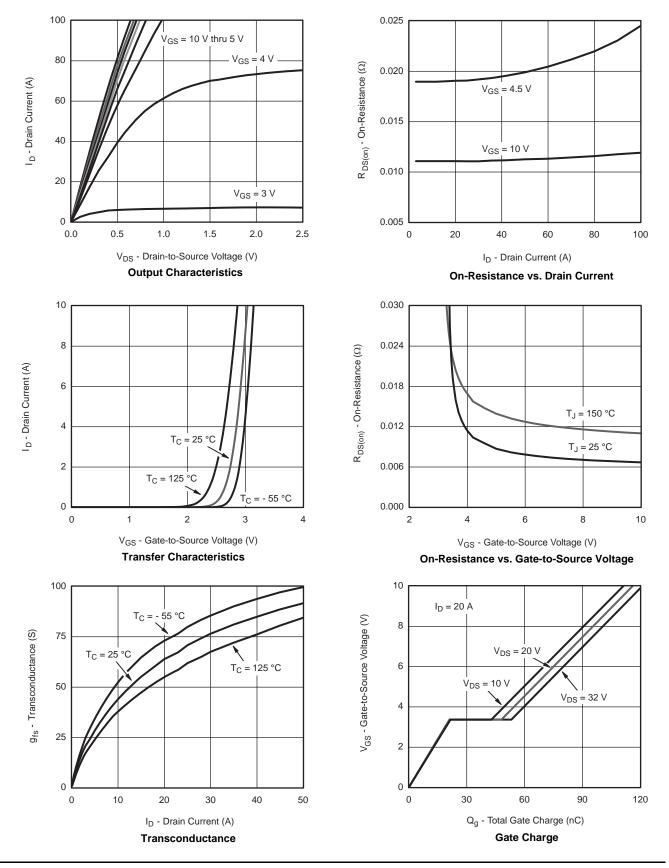
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

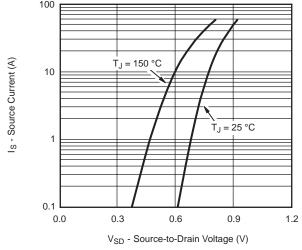


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

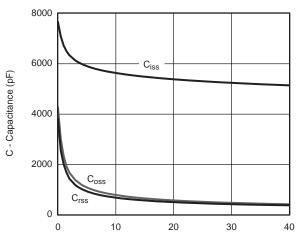




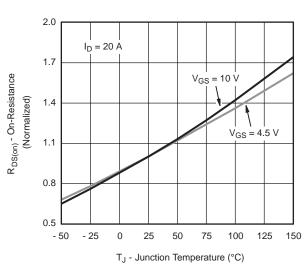
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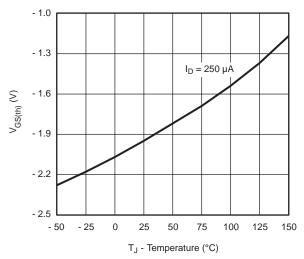
Source-Drain Diode Forward Voltage



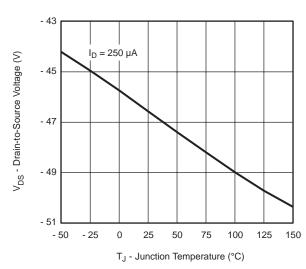
 V_{DS} - Drain-to-Source Voltage (V) ${f Capacitance}$



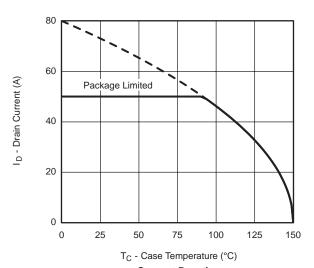
On-Resistance vs. Junction Temperature



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

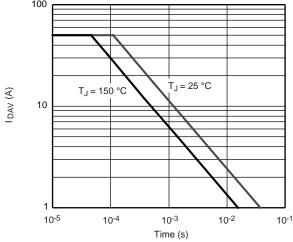


Current Derating

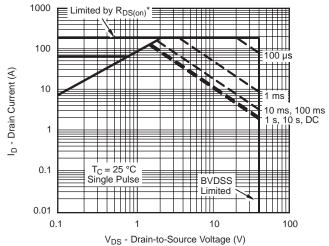


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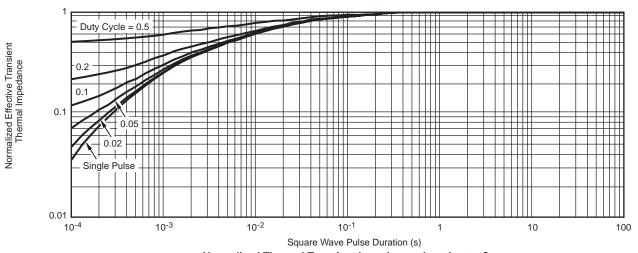


Single Pulse Avalanche Current Capability vs. Time



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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